



深圳市三联盛科技股份有限公司
SHENZHEN SLS TECHNOLOGY CO.,LTD.

股票代码 871699

SANLIANSHENG
三联盛股份

SOD-523 Plastic-Encapsulate Diode

型号：SD103AX

肖特二极管 SCHOTTKY DIODE

主要特性/Features

低正向压降 Low Forward Voltage Drop

暂态保护的保护环结构 Guard Ring Construction for Transient Protection

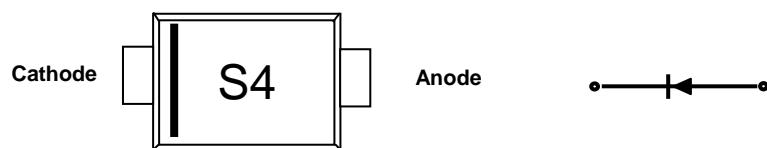
低反向恢复时间 Low Reverse Recover Time

低反向电容 Low Reverse Capacitance

应用/APPLICATION

消费电子产品 / Consumer electronics

印字/MARKING 等效电路/Equivalent Circuit





极限参数/Absolute Maximum Ratings(TA=25°Cunless otherwise noted)

Parameter	Symbol	Value	Unit
Peak Repetitive Peak Reverse Voltage	V_{RRM}	40	V
Working Peak Reverse Voltage	V_{RWM}		
DC Blocking Voltage	V_R		
RMS Reverse Voltage	$V_{R(RMS)}$	28	V
Forward Continuous current	I_o	350	mA
Repetitive Peak Forward Current @ $t \leq 1S$	I_{FRM}	1	A
Non-Repetitive Peak Forward Surge Current @ $t \leq 8.3mS$ Half Sine Wave	I_{FSM}	15	A

电性能参数/Electrical Characteristics (TA=25°Cunless otherwise noted)

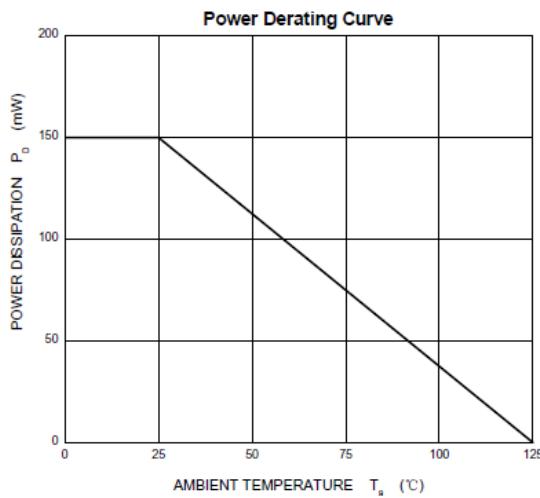
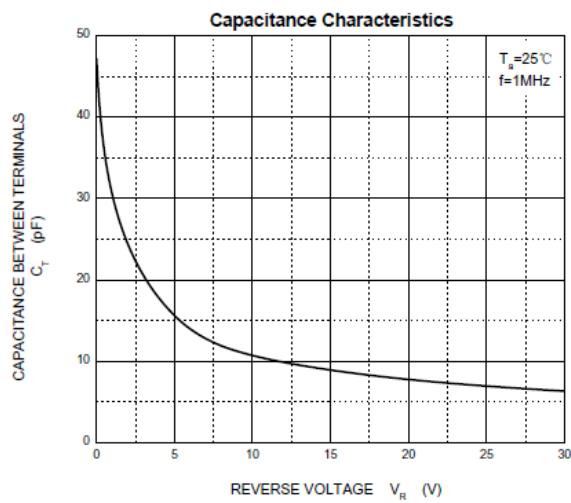
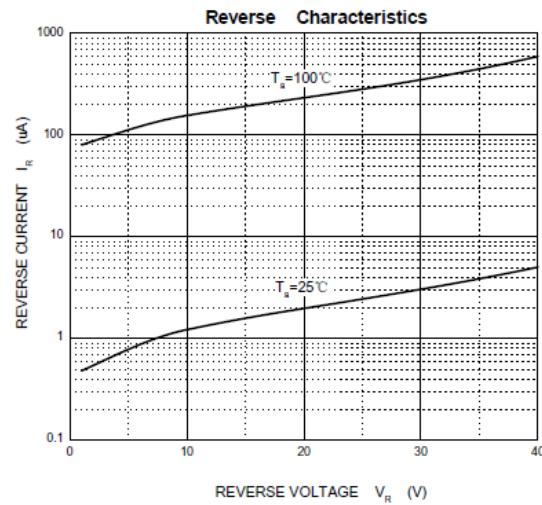
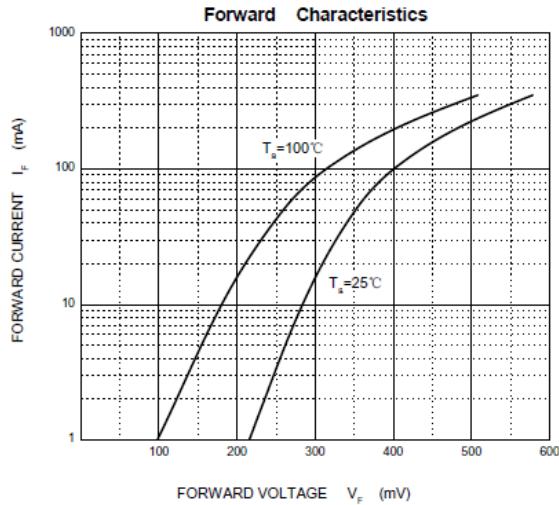
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Reverse Voltage	$V_{(BR)}$	$I_R=100\mu A$	40			V
Reverse current	I_R	$V_R=30V$			5	uA
		$V_R=20V$			2	
		$V_R=30V$			5	
		$I_F=1mA$		0.27		
Forward Voltage	V_F	$I_F=5mA$		0.32		V
		$I_F=20mA$			0.37	
		$I_F=200mA$			0.6	
Diode Capacitance	C_D	$V_R=4V, f=1.0MHz$		50		pF
Recover Reverse Time	t_{rr}	$I_F=I_R=200mA, I_{rr}=0.1 \times I_R, R_L=100\Omega$		10		nS



SANLIANSHENG
三联盛股份

SOD-523 Plastic-Encapsulate Diode

典型特性曲线图/Typical Characteristics

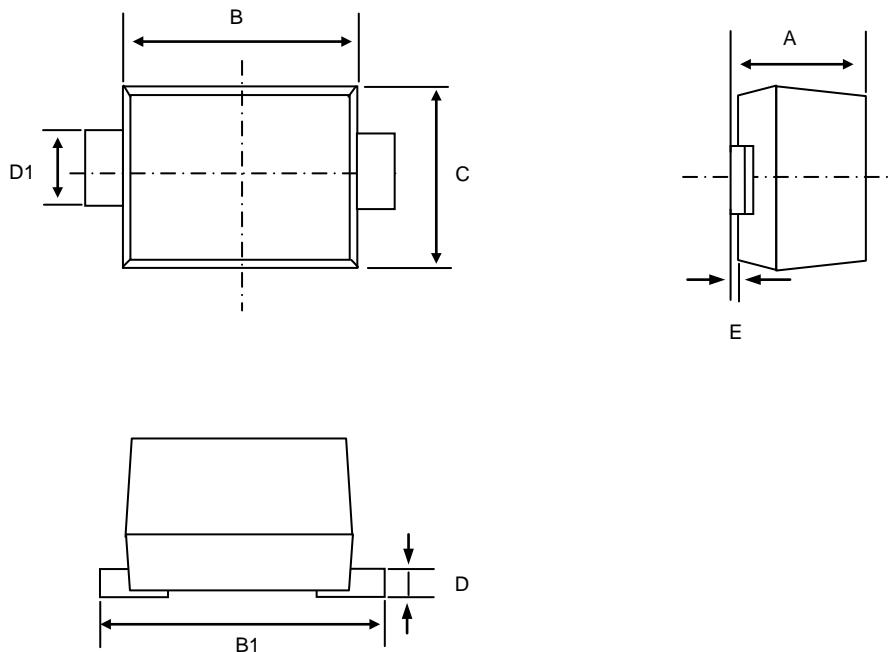




SANLIANSHENG
三联盛股份

SOD-523 Plastic-Encapsulate Diode

成品外观尺寸/SOD-523 Package Information



Symbol	Dim in mm		
	Min	Nor	Max
A	0.600	0.650	0.700
B	1.150	1.200	1.250
B1	1.550	1.600	1.650
C	0.750	0.800	0.850
D	0.100	0.110	0.120
D1	0.280	0.300	0.320
E	0.000	-	0.020